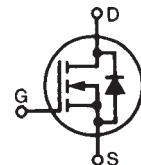


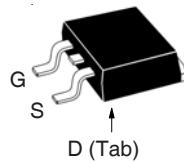
**X3-Class HiPerFET™
Power MOSFET**
IXFA80N25X3

V_{DSS} = 250V
I_{D25} = 80A
R_{DS(on)} ≤ 16mΩ



N-Channel Enhancement Mode
Avalanche Rated

TO-263



G = Gate D = Drain
 S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V _{DSS}	T _J = 25°C to 150°C	250	V
V _{DGR}	T _J = 25°C to 150°C, R _{GS} = 1MΩ	250	V
V _{GSS}	Continuous	±20	V
V _{GSM}	Transient	±30	V
I _{D25}	T _C = 25°C	80	A
I _{DM}	T _C = 25°C, Pulse Width Limited by T _{JM}	220	A
I _A	T _C = 25°C	40	A
E _{AS}	T _C = 25°C	1.2	J
dv/dt	I _S ≤ I _{DM} , V _{DD} ≤ V _{DSS} , T _J ≤ 150°C	20	V/ns
P _D	T _C = 25°C	390	W
T _J		-55 ... +150	°C
T _{JM}		150	°C
T _{stg}		-55 ... +150	°C
T _L	Maximum Lead Temperature for Soldering	300	°C
dT/dt	Heating / Cooling rate, 175°C - 210°C	50	°C/min
T _{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	°C
F _c	Mounting Force	10..65 / 2.2..14.6	N/lb
Weight		2.5	g

Features

- International Standard Package
- Low R_{DS(ON)} and Q_G
- Avalanche Rated
- Low Package Inductance

Advantages

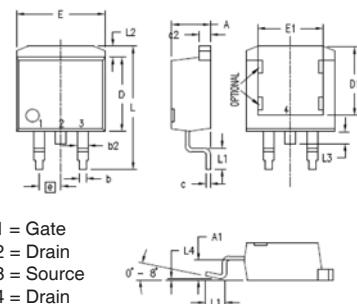
- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions (T _J = 25°C, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV _{DSS}	V _{GS} = 0V, I _D = 250μA	250		V
V _{GS(th)}	V _{DS} = V _{GS} , I _D = 1.5mA	2.5		4.5 V
I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100 nA
I _{DSS}	V _{DS} = V _{DSS} , V _{GS} = 0V T _J = 125°C			5 μA 350 μA
R _{DS(on)}	V _{GS} = 10V, I _D = 0.5 • I _{D25} , Note 1			16 mΩ

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
g_{fs}	$V_{DS} = 10\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1	38	64	S
R_{GI}	Gate Input Resistance		1.6	Ω
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$	5430		pF
C_{oss}		890		pF
C_{rss}		1.6		pF
Effective Output Capacitance				
$C_{o(er)}$	Energy related } $V_{GS} = 0\text{V}$	320		pF
$C_{o(tr)}$	Time related } $V_{DS} = 0.8 \cdot V_{DSS}$	1410		pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 5\Omega$ (External)	30		ns
t_r		17		ns
$t_{d(off)}$		65		ns
t_f		8		ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$	83		nC
Q_{gs}		27		nC
Q_{gd}		24		nC
R_{thJC}			0.32	$^\circ\text{C}/\text{W}$

TO-263 (IXFA) Outline

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100	BSC	2.54	BSC
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
I_s	$V_{GS} = 0\text{V}$		80	A
I_{SM}	Repetitive, pulse Width Limited by T_{JM}		320	A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{V}$, Note 1		1.4	V
t_{rr}	$I_F = 40\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$	120		ns
Q_{RM}		600		nC
I_{RM}		10		A

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065B1 6,683,344 6,727,585 7,005,734B2 7,157,338B2 4,860,072 5,017,508 5,063,307 5,381,025 6,259,123B1 6,534,343 6,710,405B2 6,759,692 7,063,975B2 4,881,106 5,034,796 5,187,117 5,486,715 6,306,728B1 6,583,505 6,710,463 6,771,478B2 7,071,537

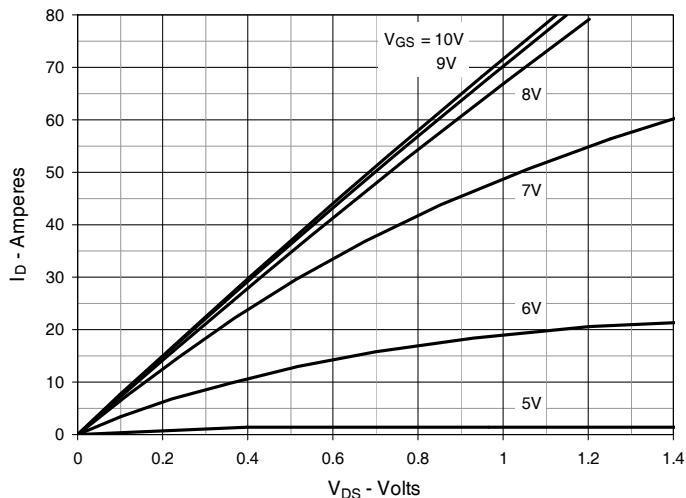
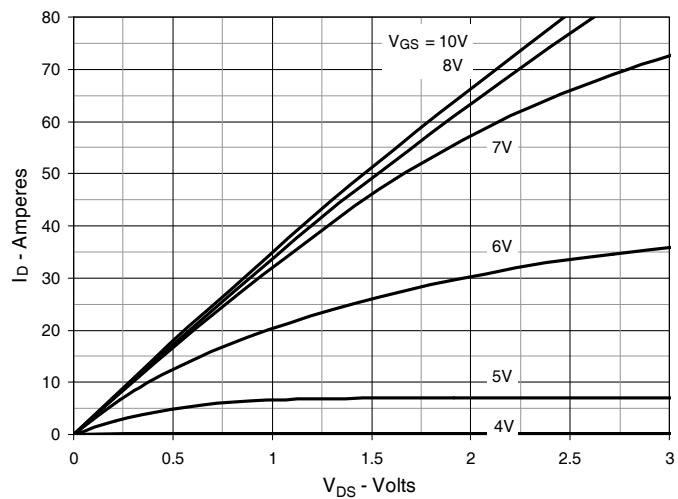
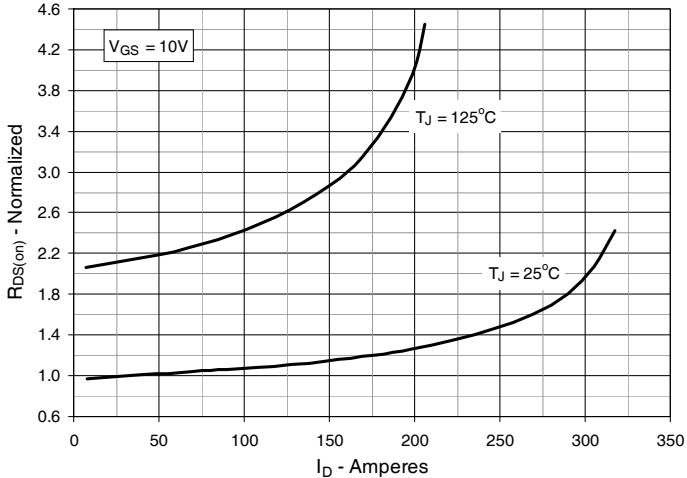
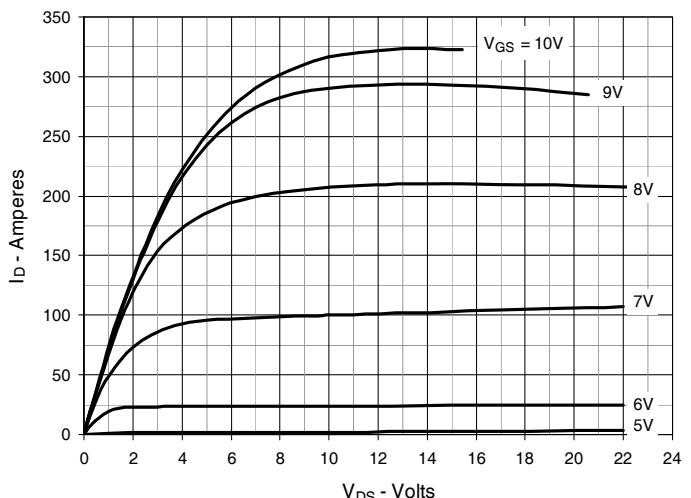
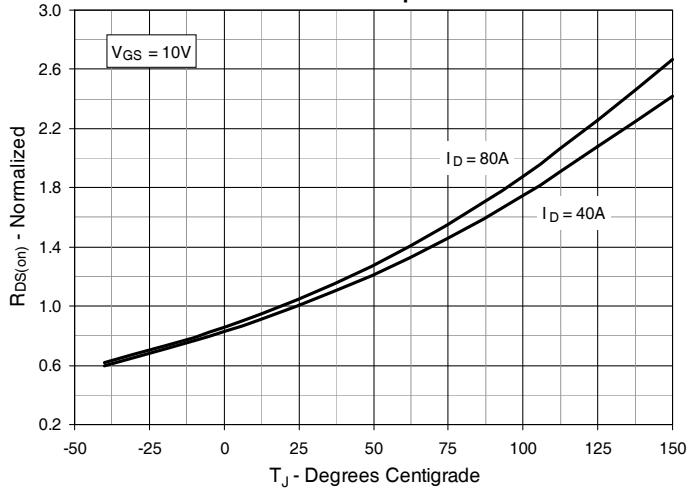
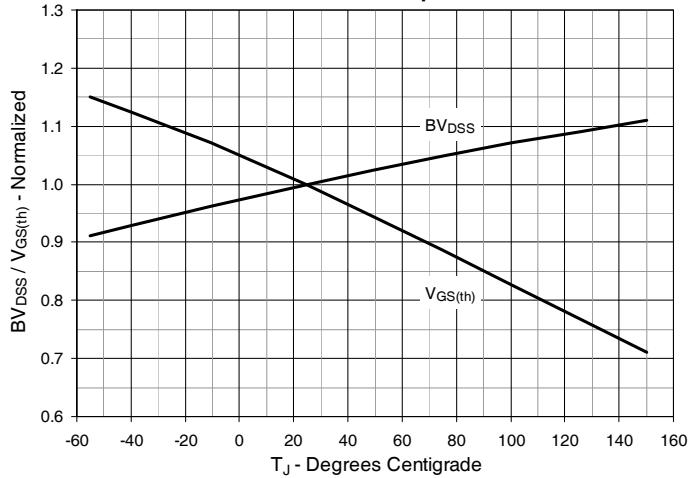
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$ **Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$** **Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 40\text{A}$ Value vs. Drain Current****Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$** **Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 40\text{A}$ Value vs. Junction Temperature****Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature**

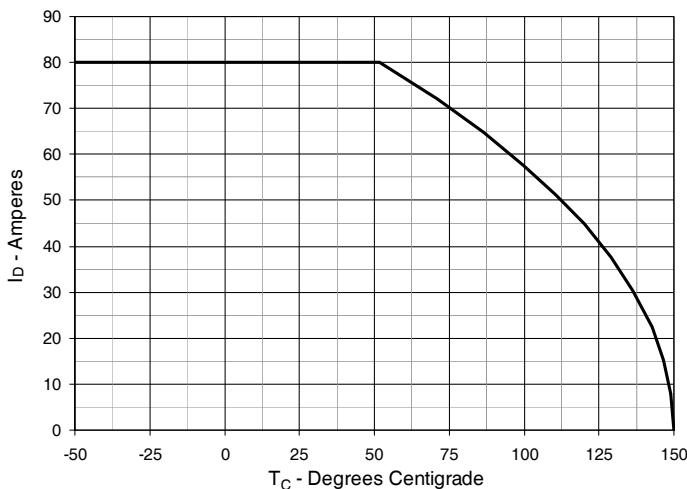
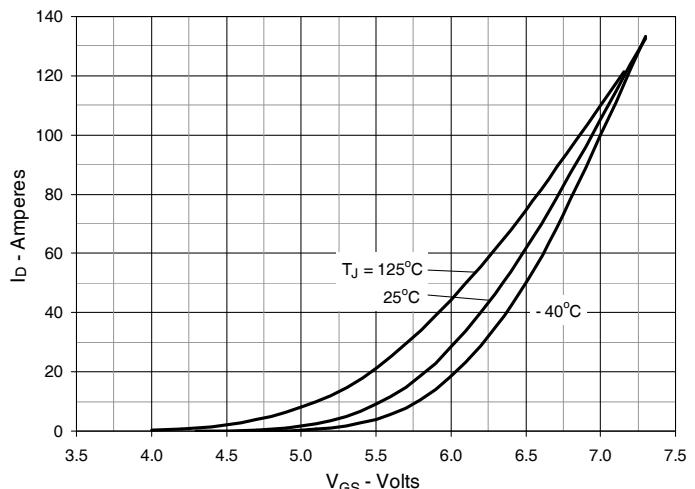
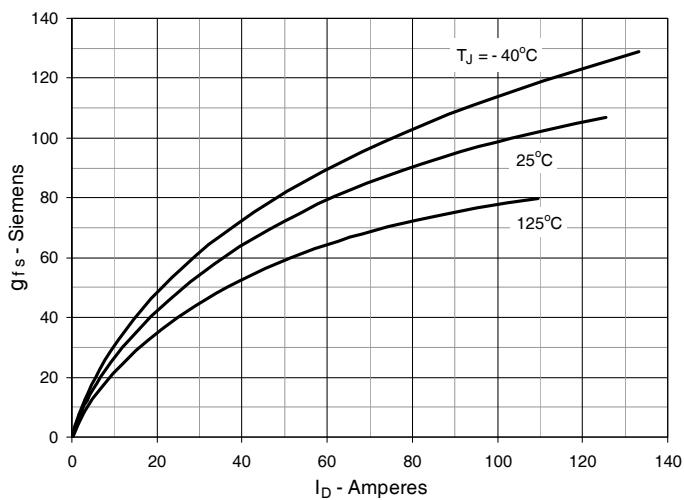
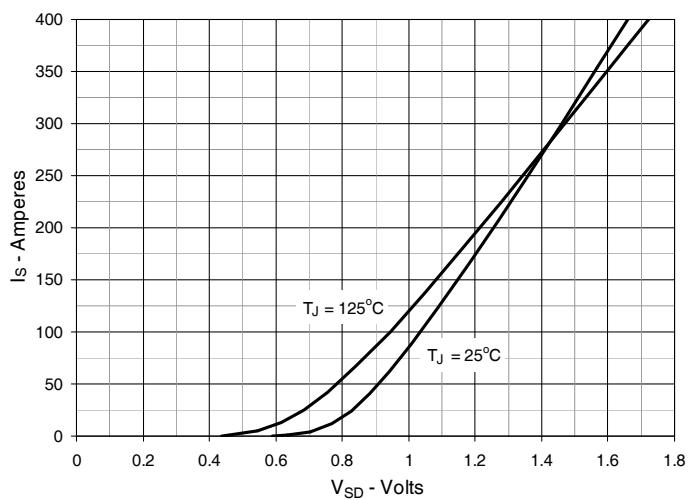
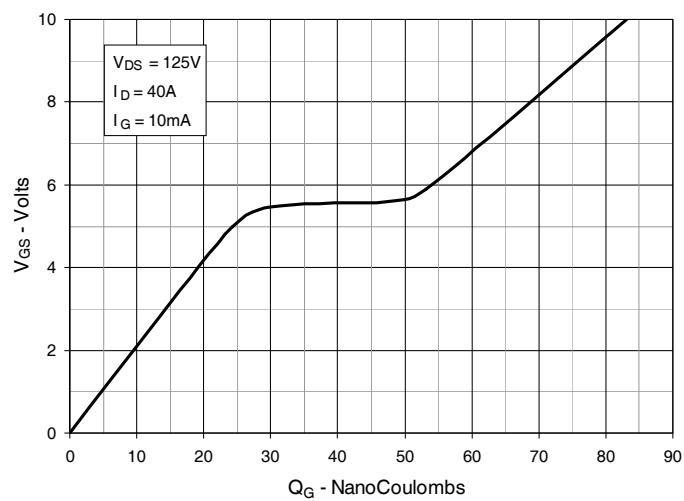
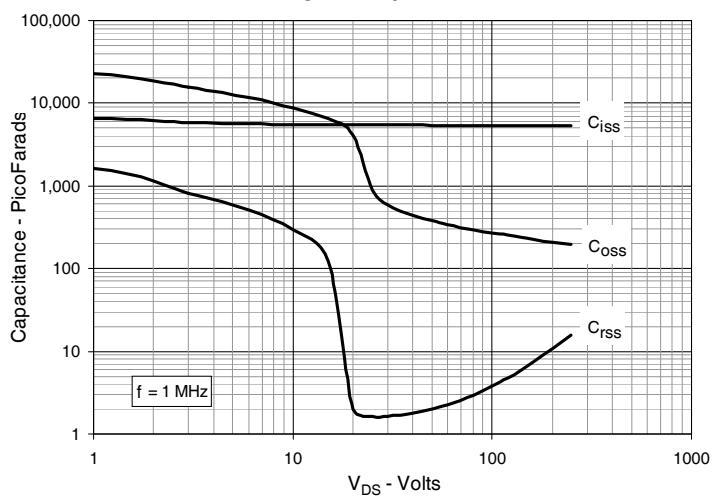
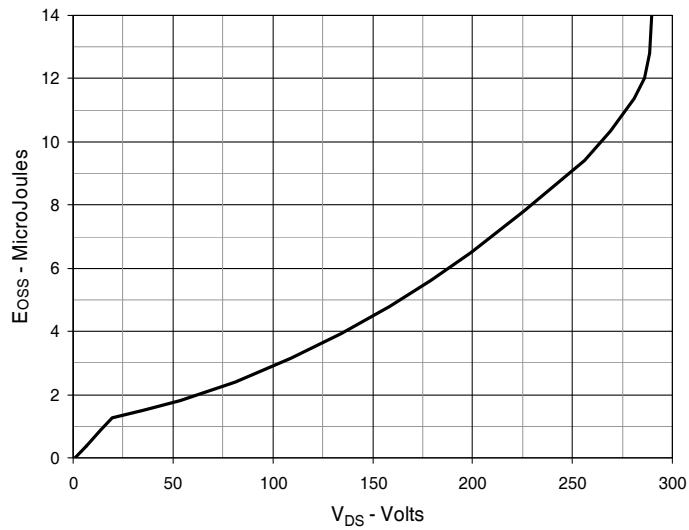
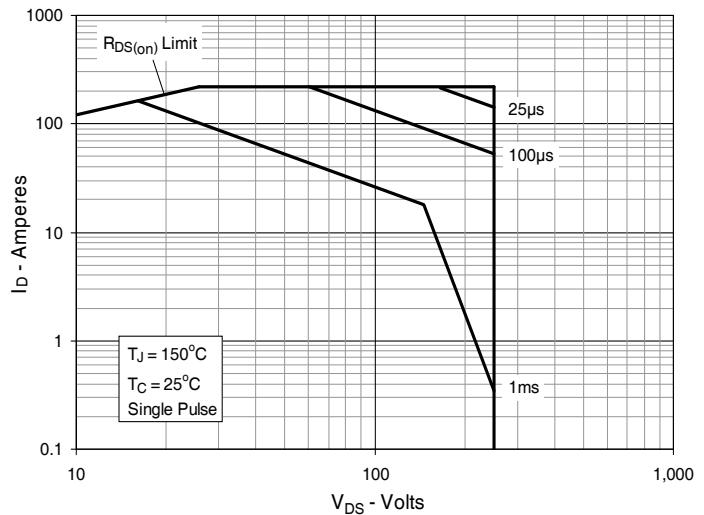
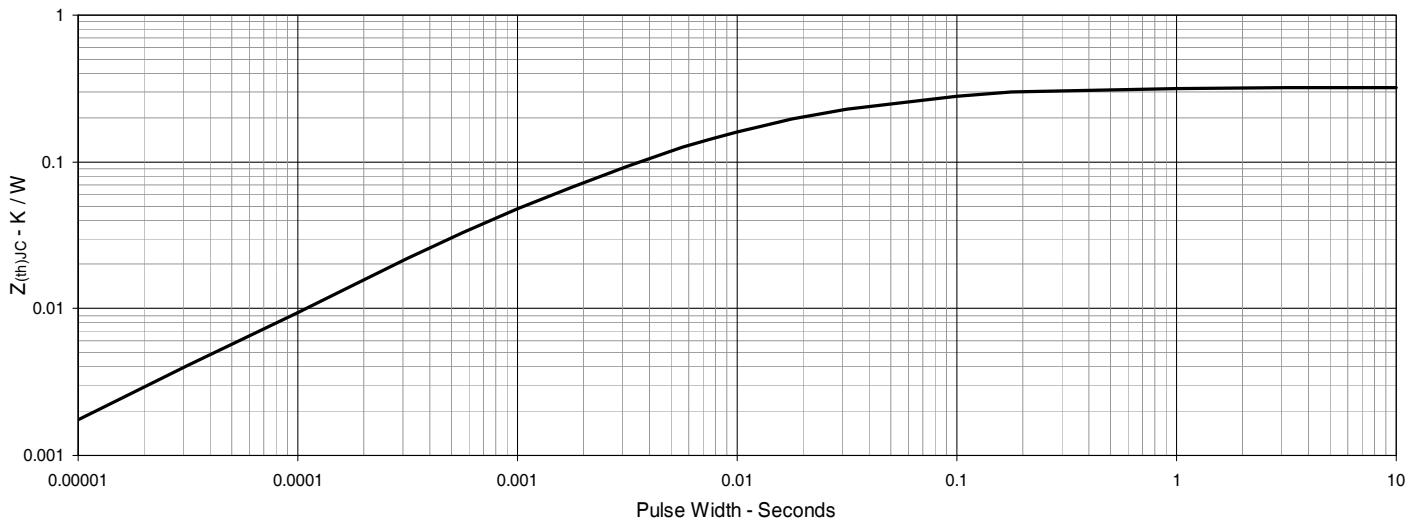
Fig. 7. Maximum Drain Current vs. Case Temperature**Fig. 8. Input Admittance****Fig. 9. Transconductance****Fig. 10. Forward Voltage Drop of Intrinsic Diode****Fig. 11. Gate Charge****Fig. 12. Capacitance**

Fig. 13. Output Capacitance Stored Energy**Fig. 14. Forward-Bias Safe Operating Area****Fig. 15. Maximum Transient Thermal Impedance**

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